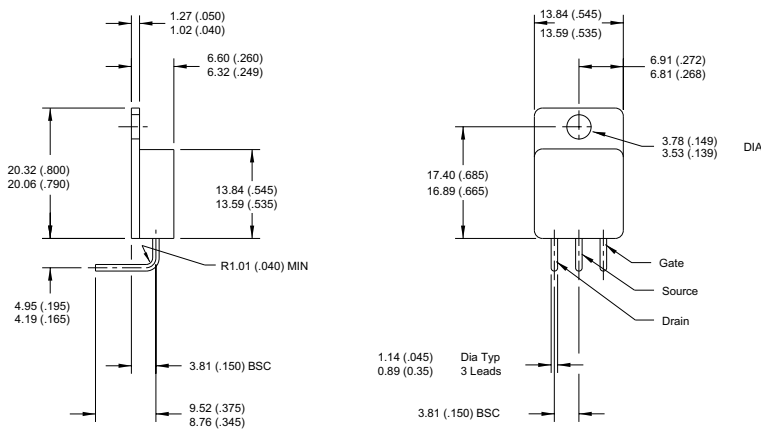


TO-254 Package Outline.
Dimensions in mm (inches)



4TH GENERATION MOSFET

**N-CHANNEL
ENHANCEMENT MODE
HIGH VOLTAGE
ISOLATED
POWER MOSFETS**

V_{DSS} 1000V
 $I_{D(cont)}$ 3.3A
 $R_{DS(on)}$ 4.20 Ω

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{DSS}	Drain – Source Voltage	1000	V
I_D	Continuous Drain Current	3.0	A
I_{DM}	Pulsed Drain Current ¹	13.2	A
V_{GS}	Gate – Source Voltage	± 30	V
P_D	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	125	W
	Linear Derating Factor	1.0	W / $^{\circ}C$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^{\circ}C$
T_L	Lead Temperature : 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	1000			V
$I_{D(ON)}$	On State Drain Current ²	$V_{DS} > I_{D(ON)} \times R_{DS(ON)}$ Max $V_{GS} = 10V$	3.3			A
$R_{DS(ON)}$	Drain – Source On State Resistance ²	$V_{GS} = 10V, I_D = 0.5 I_D [Cont.]$			4.20	Ω
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0V$)	$V_{DS} = V_{DSS}$			250	μA
		$V_{DS} = 0.8V_{DSS}, T_C = 125^{\circ}C$			1000	
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1.0mA$	2		4	V

1) Repetitive Rating: Pulse Width limited by maximum junction temperature.

2) Pulse Test: Pulse Width < 380mS , Duty Cycle < 2%

DYNAMIC CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
C_{DC}	Drain to Case Capacitance	$f = 1\text{MHz}$		15	22	pF
C_{iss}	Input Capacitance	$V_{GS} = 0V$		805	950	pF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		115	160	
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		37	60	
Q_g	Total Gate Charge ³	$V_{GS} = 10V$		35	55	nC
Q_{gs}	Gate – Source Charge	$V_{DD} = 0.5 V_{DSS}$		4.3	7	
Q_{gd}	Gate – Drain (“Miller”) Charge	$I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$		18	27	
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$		10	20	ns
t_r	Rise Time	$V_{DD} = 0.5 V_{DSS}$		12	24	
$t_{d(off)}$	Turn-off Delay Time	$I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$		33	50	
t_f	Fall Time	$R_G = 1.8\Omega$		16	32	

SOURCE – DRAIN DIODE RATINGS AND CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current (Body Diode)				3.3	A
I_{SM}	Pulsed Source Current ¹ (Body Diode)				12	
V_{SD}	Diode Forward Voltage ²	$V_{GS} = 0V, I_S = -I_D [\text{Cont.}]$			1.3	V
t_{rr}	Reverse Recovery Time	$I_S = -I_D [\text{Cont.}]$	150	290	580	ns
Q_{rr}	Reverse Recovery Charge	$di_S / dt = 100A/ms$	0.8	1.65	3.3	μC

SAFE OPERATING AREA CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
SOA1	Safe Operating Area , $t = 1 \text{ Sec}$	$V_{DS} = 0.4V_{DSS}, I_{DS} = P_D / 0.4V_{DSS}$	125			W
SOA2	Safe Operating Area , $t = 1 \text{ Sec}$	$V_{DS} = P_D / I_D [\text{Cont.}], I_{DS} = I_D [\text{Cont.}]$	125			
I_{LM}	Inductive Current Clamped		13.2			A

THERMAL CHARACTERISTICS

	Characteristic	Min.	Typ.	Max.	Unit
R_{qJC}	Junction to Case			1.0	$^\circ\text{C/W}$
R_{qJA}	Junction to Ambient			50	

1) Repetitive Rating: Pulse Width limited by maximum junction temperature.

2) Pulse Test: Pulse Width < 380ms , Duty Cycle < 2%

3) See MIL-STD-750 Method 3471



CAUTION — Electrostatic Sensitive Devices. Anti-Static Procedures Must Be Followed.